

	Hits	Search Text	DBs
1	8	mems and delayed adj locos	USPAT; US-PGPUB; EPO; JPO; DERWENT;
2	62	mems and locos	USPAT; US-PGPUB; EPO; JPO; DERWENT;
3	54	(mems and locos) not (mems and delayed adj locos)	USPAT; US-PGPUB; EPO; JPO; DERWENT;
4	8	((mems and locos) not (mems and delayed adj locos)) and (si3n4 "Si.sub.3 N.sub.4" nitride) and thermal\$3 adj oxid\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	2	("6464892").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;
6	15	("4764244"   "4911783"   "5006202"   "5131978"   "5332469"   "5542558"   "5628917"   "5658471"   "5683591"   "5690841"   "5717251"   "5770465"   "6020272"   "6174820"	USPAT
7	2	("6444138").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;
8	8	("4911783"   "5006202"   "5131978"   "5717251"   "5770465"   "6020272"   "6136243"   "6174820").PN.	USPAT
9	7	((("4764244"   "4911783"   "5006202"   "5131978"   "5332469"   "5542558"   "5628917"   "5658471"   "5683591"   "5690841"   "5717251"   "5770465"   "6020272"   "6174820"   "6136243").PN.) not (("4911783"   "5006202"   "5131978"   "5717251"   "5770465"   "6020272"   "6136243"   "6174820").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	8	mems and latent adj mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT;
11	3999	(MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj	USPAT; US-PGPUB; EPO; JPO; DERWENT;
12	2480	((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side) ) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	1440	((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side) ) and etch\$3) and (photoresist resist photomask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	1126	(((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side) ) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	906	((((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side) ) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side) ) and (MEMS wafer substrate workpiece silicon) with oxide with (((first and second) both) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	330	((((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side) ) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side) ) and (MEMS wafer substrate workpiece silicon) with oxide with (((first and second) both) adj side) ) and (MEMS wafer substrate workpiece silicon) near oxide with (((first and second) both) adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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17	17	(((((MEMS wafer substrate workpiece silicon) and oxide with (((first and second) both) adj side) ) and etch\$3) and (photoresist resist photomask\$3)) and (MEMS wafer substrate workpiece silicon) same oxide with (((first and second) both) adj side) ) and (MEMS wafer substrate workpiece silicon) with oxide with (((first and second) both) adj side) ) and (MEMS wafer substrate workpiece silicon) near oxide with (((first and second) both) adj side) ) and (MEMS wafer substrate workpiece silicon) near oxide near (((first and second) both) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	18	SMILE and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT;
19	9	((multilevel multi-level) near etch\$3) and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT;
20	15	("4764244"   "4911783"   "5006202"   "5131978"   "5332469"   "5542558"   "5628917"   "5658471"   "5683591"   "5690841"   "5717251"   "5770465"   "6020272"   "6174820"	USPAT
21	0	((("4764244"   "4911783"   "5006202"   "5131978"   "5332469"   "5542558"   "5628917"   "5658471"   "5683591"   "5690841"   "5717251"   "5770465"   "6020272"   "6174820"   "6136243").PN. ) and locos	USPAT
22	1	((("4764244"   "4911783"   "5006202"   "5131978"   "5332469"   "5542558"   "5628917"   "5658471"   "5683591"   "5690841"   "5717251"   "5770465"   "6020272"   "6174820"   "6136243").PN. ) and latent	USPAT
23	0	((("4764244"   "4911783"   "5006202"   "5131978"   "5332469"   "5542558"   "5628917"   "5658471"   "5683591"   "5690841"   "5717251"   "5770465"   "6020272"   "6174820"   "6136243").PN. ) and smile	USPAT
24	52	MEMS and (smile locos latent adj mask\$3)	USPAT
25	9	MEMS and smile	USPAT
26	2	MEMS and delayed adj locos	USPAT
27	45	MEMS and locos	USPAT
28	2	MEMS and latent adj mask\$3	USPAT
29	41	latent adj mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT;
30	295	mem and ((oxide hard) near (mask resist))	USPAT; US-PGPUB; EPO; JPO; DERWENT;
31	182	(mem and ((oxide hard) near (mask resist))) and (backside (back bottom) near3 (wafer substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32	100	(mem and ((oxide hard) near (mask resist))) and (backside (back bottom) near3 (wafer substrate) near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
33	96	(mem and ((oxide hard) near (mask resist))) and (backside (back bottom) near (wafer substrate) near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	96	(mem and ((oxide hard) near (mask resist))) and (backside (back bottom) adj (wafer substrate) near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	1	(mem and ((oxide hard) near (mask resist))) and ((backside (back bottom)) adj (wafer substrate) near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36	11	(mem and ((oxide hard) near (mask resist))) and ((backside (back bottom)) near3 (wafer substrate) near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
37	47	(mem and ((oxide hard) near (mask resist))) and ((backside (back bottom)) with (wafer substrate) with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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38	36	((mem and ((oxide hard) near (mask resist))) and ((backside (back bottom)) with (wafer substrate) with oxide)) not ((mem and ((oxide hard) near (mask resist))) and ((backside (back bottom)) near3 (wafer substrate) near3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
39	75	((mem and ((oxide hard) near (mask resist))) and (backside (back bottom) adj (wafer substrate) near oxide)) not ((mem and ((oxide hard) near (mask resist))) and ((backside (back bottom)) with (wafer substrate) with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB